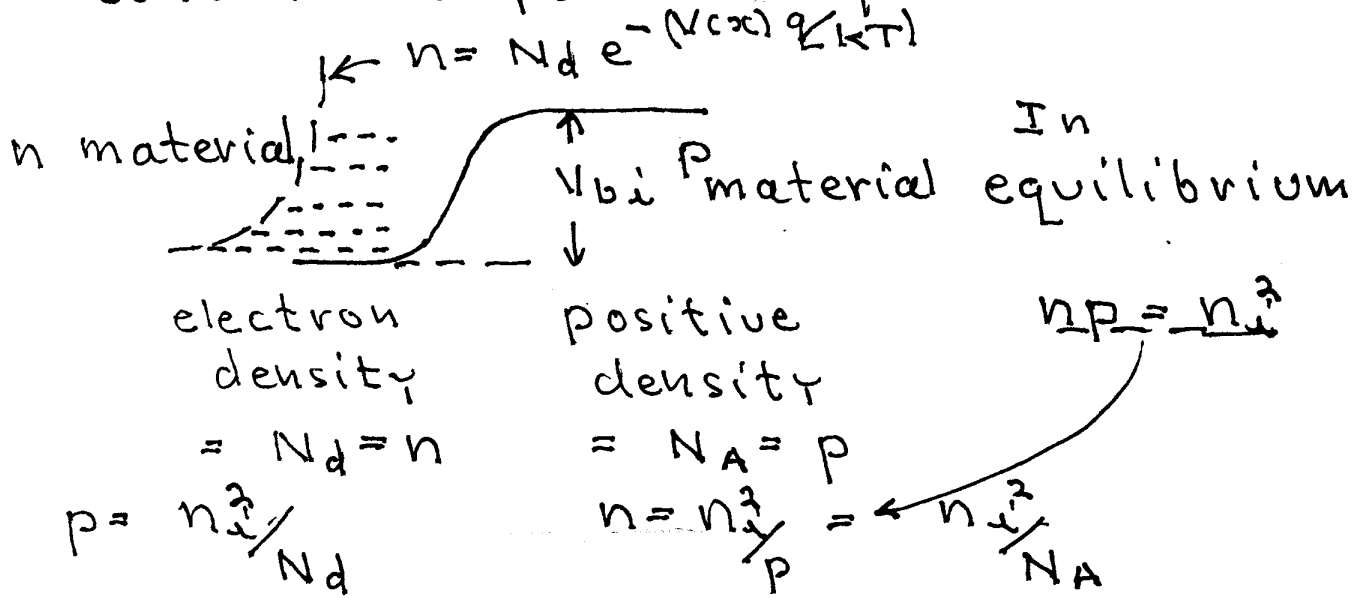


The Diode Equation

Consider a potential profile



$$n(\text{in p material}) = \frac{n_i^2}{N_A} = N_d e^{-\frac{V_{bi}q}{kT}}$$

Lower V_{bi} by applying a bias

$$n(\text{in p material}) = N_d e^{-(V_{bi}-V)q/kT}$$

$$= \frac{n_i^2}{N_A} e^{+Vq/kT}$$

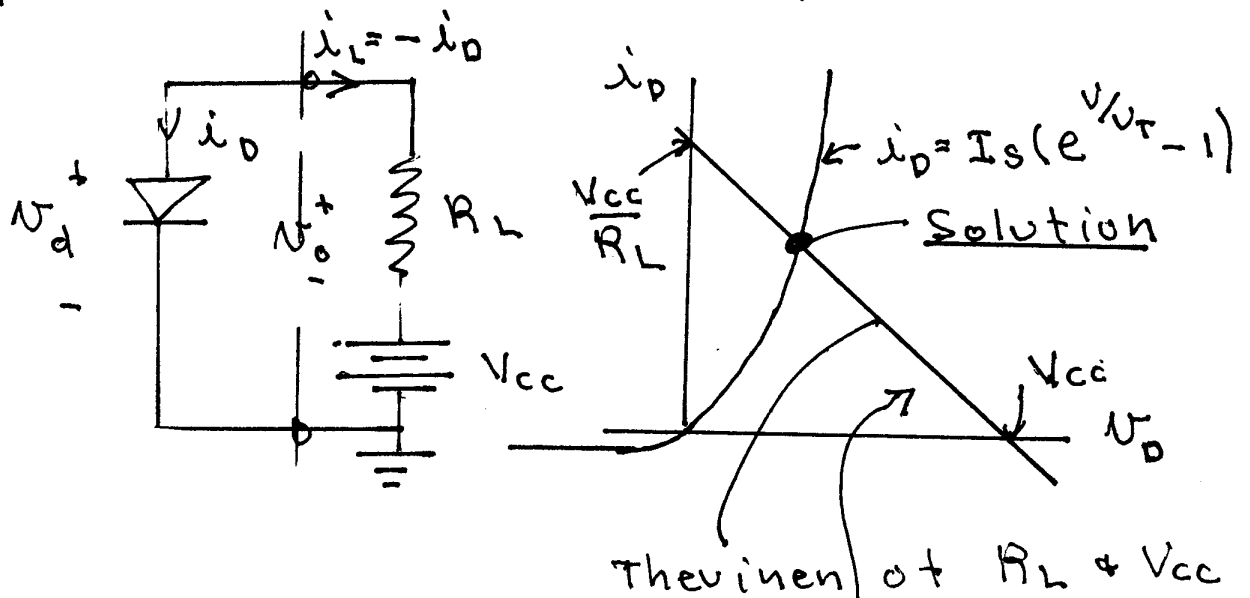
As we penetrate the p material the excess electrons exponentially combine

$$n(x) = \frac{n_i^2}{N_A} e^{Vq/kT} e^{-x/L_n} - \frac{n_i^2}{N_A} (e^{-x/L_n} - 1)$$

$$\text{Current} = (\text{Area}) \times D_n q \frac{dn}{dx} \Big|_{(At x=0)}$$

$$= +A D_n q \frac{n_i^2}{N_A} (e^{qV/kT} - 1)$$

Simple Diode Problem - Graphical Solution



$$V_D = V_L = i_L R_L + V_{cc} \\ = -i_D R_L + V_{cc}$$

or

$$i_D = -\frac{V_D}{R_L} + \frac{V_{cc}}{R_L}$$

Can find this numerically by successive approximations (Newton-Raphson for example)